

## 1. General description

Planar passivated Silicon Controlled Rectifier in a SOT429N (TO247) plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance.

## 2. Features and benefits

- High thermal cycling performance
- Planar passivated for voltage ruggedness and reliability
- High voltage capacity
- Very high current surge capability

## 3. Applications

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control
- Uninterruptible Power Supply (UPS)
- Solid State Relay (SSR)
- Traction battery charging

## 4. Quick reference data

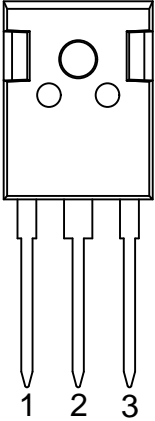

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	1200	V
$V_{RRM}$	repetitive peak reverse voltage		-	-	1200	V
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	1100	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 8.3\text{ ms}$	-	-	1210	A
$T_j$	junction temperature		-	-	150	°C
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 117\text{ °C}$	-	-	80	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 117\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	126	A

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 7</a> ; <a href="#">Fig. 8</a>	-	-	70	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 800\text{ V}$ ; $T_j = 125\text{ °C}$ ; $R_{GK} = 100\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	1500	-	-	V/ $\mu$ s

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p>TO-247 (SOT429N)</p>	 <p>sym037</p>
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

## 6. Ordering information

Table 3. Ordering information

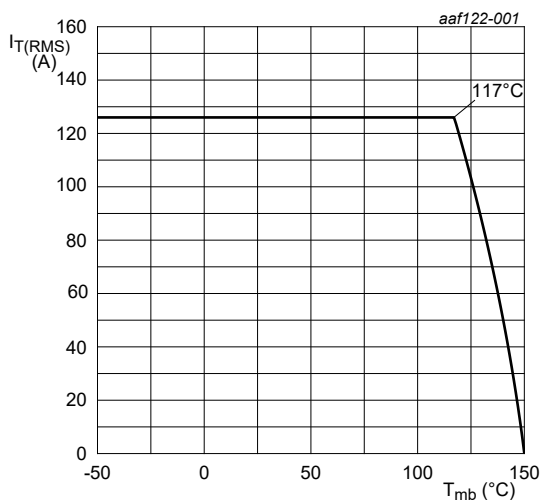
Type number	Package		Version
	Name	Description	
BT158W-1200T	TO-247	Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247	SOT429N

## 7. Limiting values

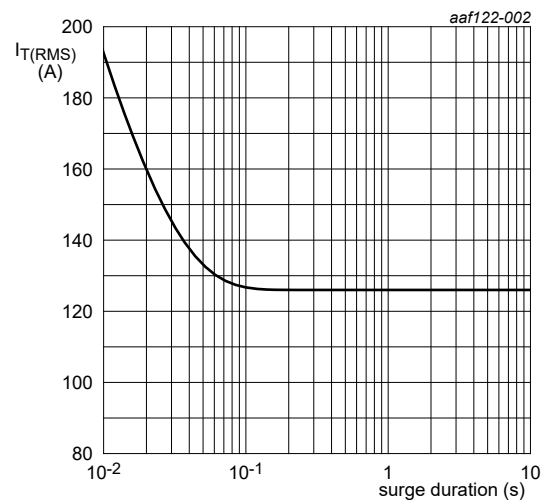
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	1200	V
$V_{RRM}$	repetitive peak reverse voltage		-	1200	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 117\text{ }^{\circ}\text{C}$	-	80	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 117\text{ }^{\circ}\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	126	A
$I_{TSM}$	non-repetitive peak on-state current	half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 10\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	1100	A
		half sine wave; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; $t_p = 8.3\text{ ms}$	-	1210	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse; $T_{j(\text{init})} = 25\text{ }^{\circ}\text{C}$ ; no voltage reapplied	-	6115	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 200\text{ mA}$	-	150	A/ $\mu\text{s}$
$I_{GM}$	peak gate current		-	8	A
$V_{RGM}$	peak reverse gate voltage		-	5	V
$P_{GM}$	peak gate power		-	20	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
$T_{stg}$	storage temperature		-40	150	$^{\circ}\text{C}$
$T_j$	junction temperature		-	150	$^{\circ}\text{C}$



**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

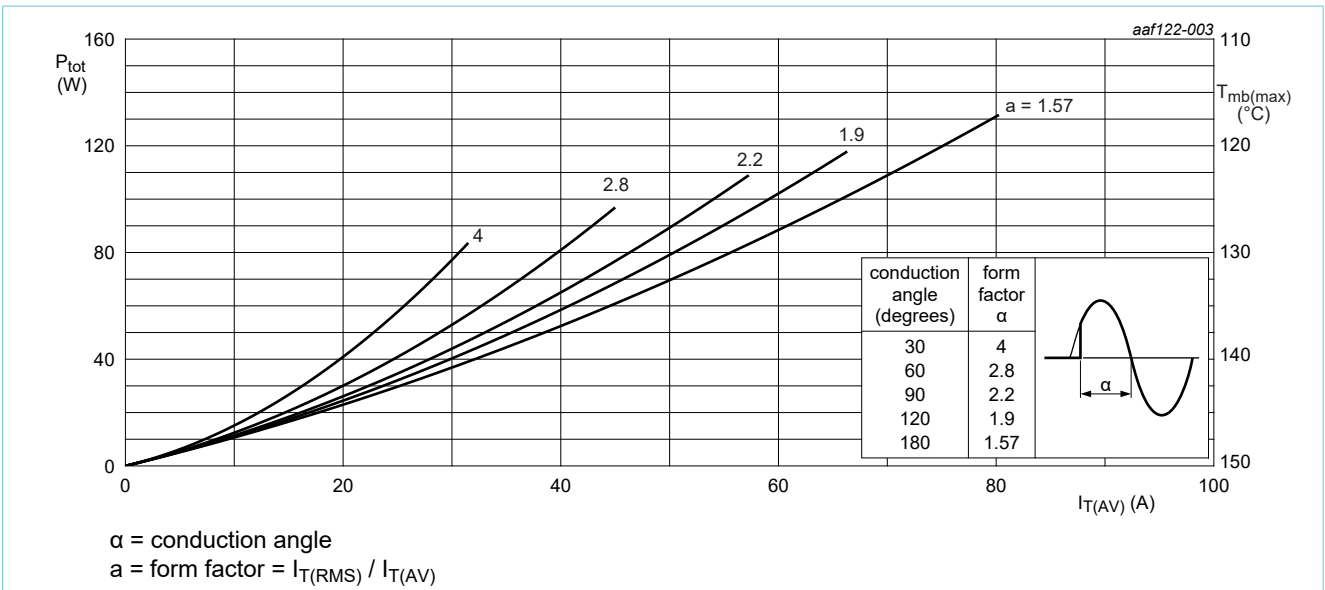


Fig. 3. Total power dissipation as a function of average on-state current; maximum values

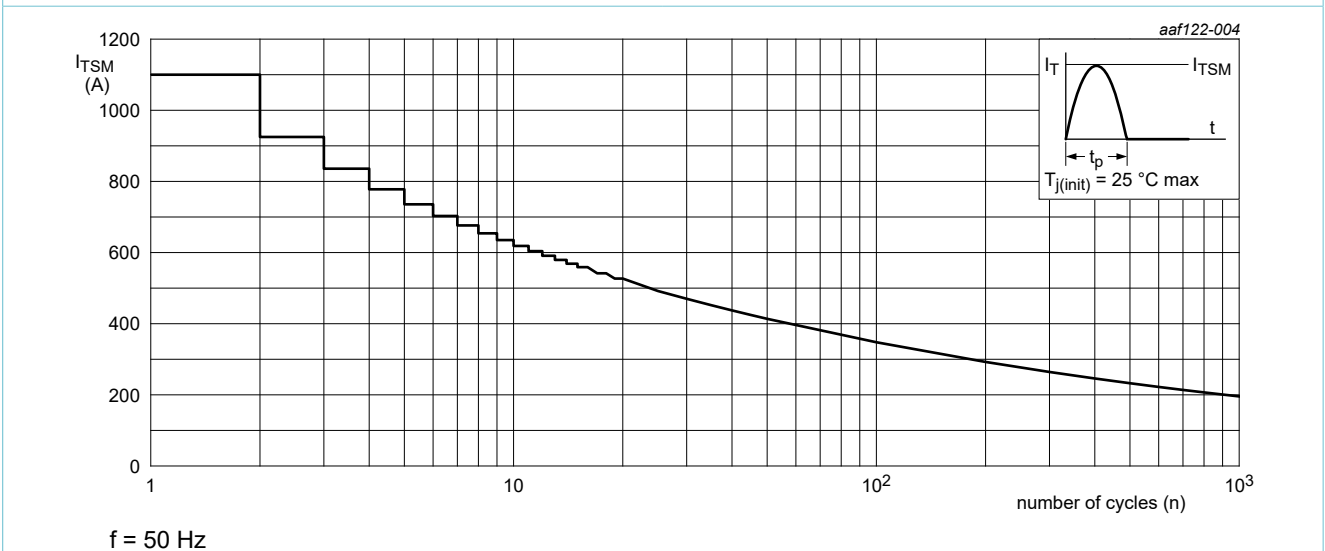
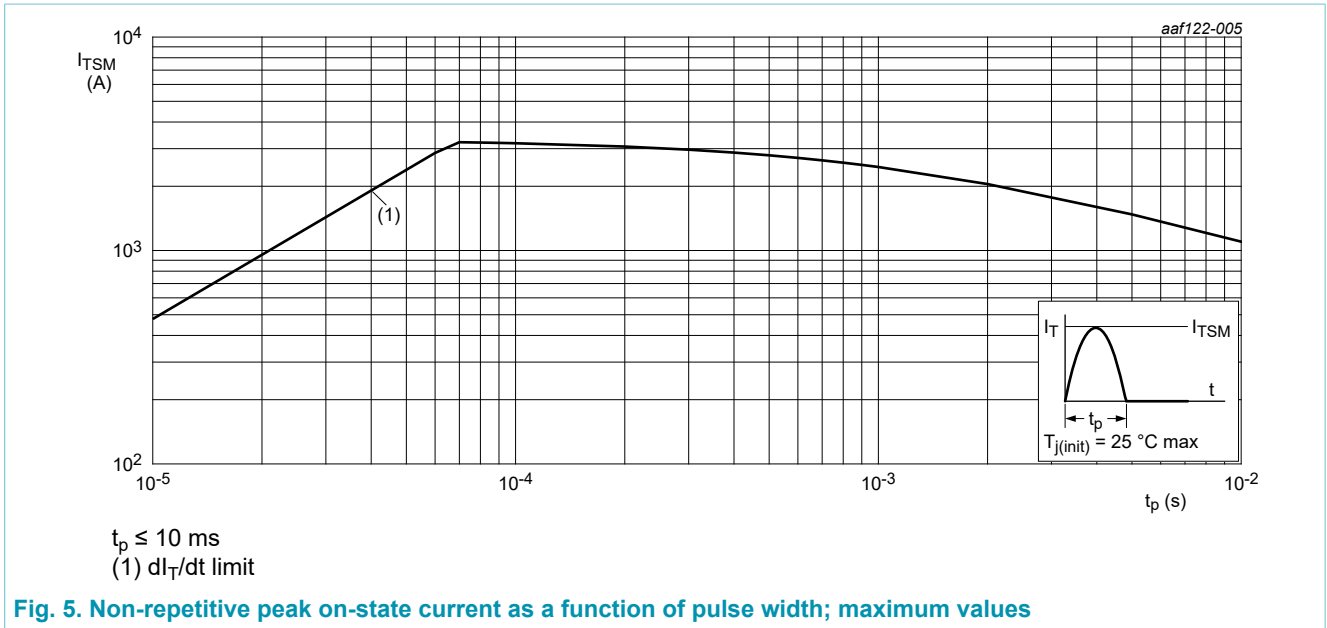


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; <a href="#">Fig. 6</a>	-	-	0.25	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W

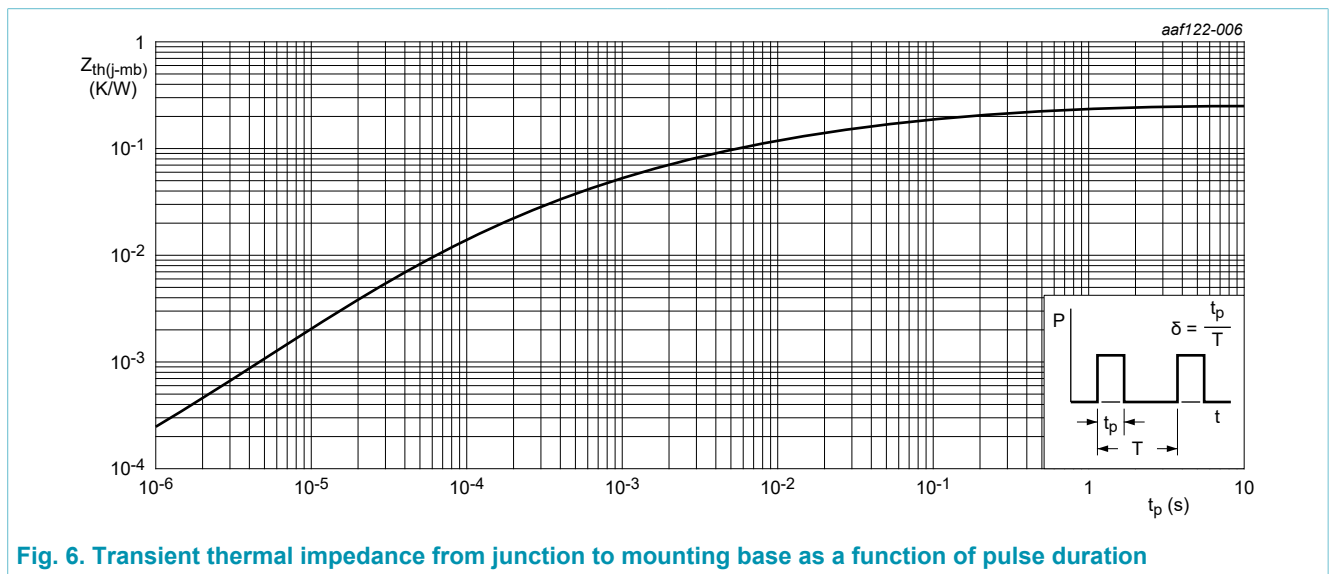


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a> ; <a href="#">Fig. 8</a>	-	-	70	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 9</a>	-	-	300	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>	-	-	200	mA
$V_T$	on-state voltage	$I_T = 80\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	-	1.35	V
		$I_T = 160\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>	-	-	1.65	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	-	0.7	1	V
		$V_D = 800\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 12</a>	0.25	0.4	-	V
$I_D$	off-state current	$V_D = 1200\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	-	3	mA
$I_R$	reverse current	$V_R = 1200\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$	-	-	3	mA
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 800\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $R_{GK} = 100\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	1500	-	-	V/ $\mu\text{s}$
		$V_{DM} = 800\text{ V}$ ; $T_j = 150\text{ }^\circ\text{C}$ ; $R_{GK} = 100\text{ }\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform	1000	-	-	V/ $\mu\text{s}$
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 40\text{ A}$ ; $V_D = 800\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$ ; $T_j = 25\text{ }^\circ\text{C}$	-	2	-	$\mu\text{s}$
$t_q$	commutated turn-off time	$V_{DM} = 804\text{ V}$ ; $T_j = 125\text{ }^\circ\text{C}$ ; $I_{TM} = 20\text{ A}$ ; $V_R = 25\text{ V}$ ; $(dI_T/dt)_M = 30\text{ A}/\mu\text{s}$ ; $dV_D/dt = 50\text{ V}/\mu\text{s}$ ; $R_{GK(ext)} = 100\text{ k}\Omega$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ )	-	150	-	$\mu\text{s}$

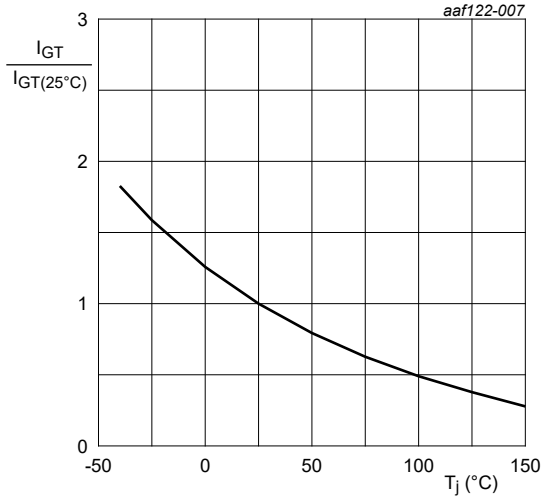


Fig. 7. Normalized gate trigger current as a function of junction temperature

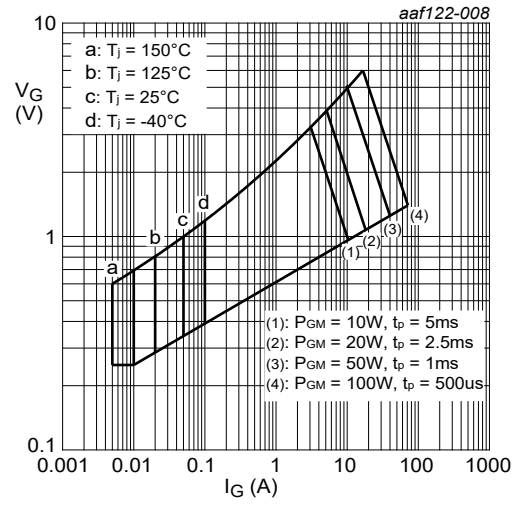


Fig. 8. Gate voltage as a function of gate current

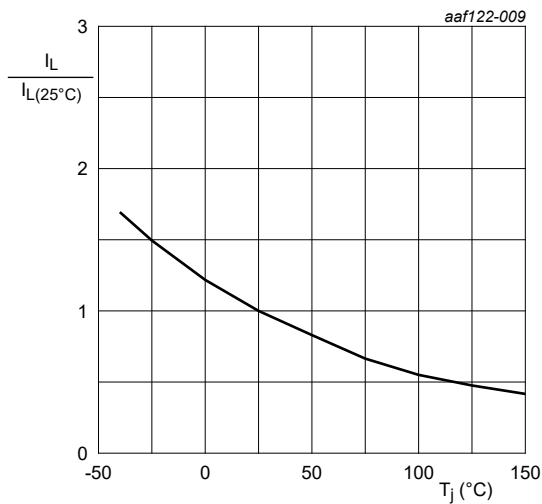


Fig. 9. Normalized latching current as a function of junction temperature

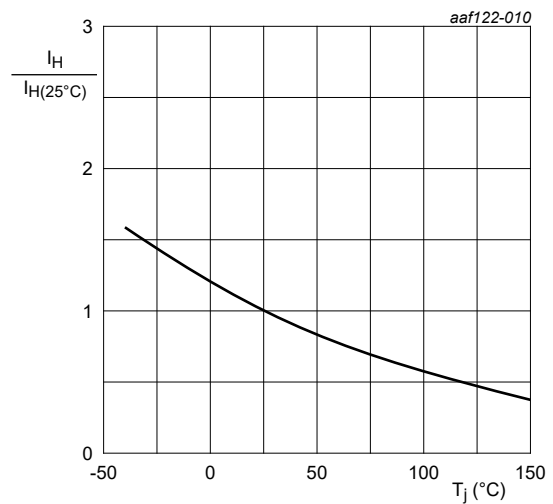
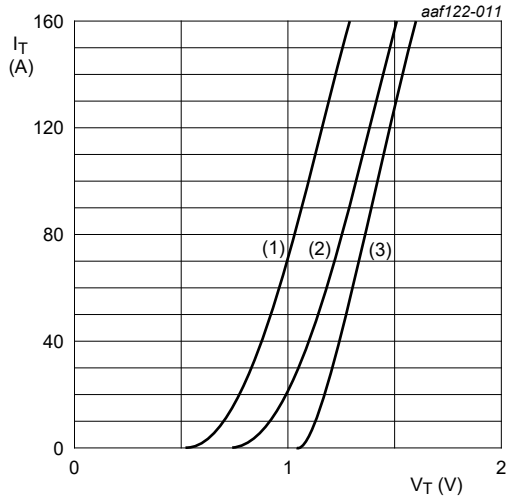


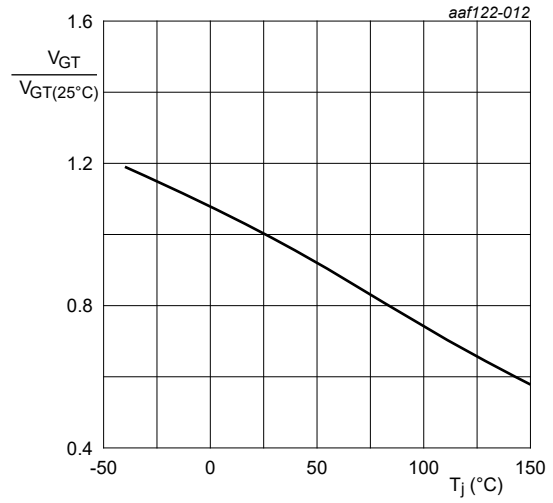
Fig. 10. Normalized holding current as a function of junction temperature





$V_o = 0.984 \text{ V}; R_s = 0.0033 \Omega$   
 (1)  $T_j = 150 \text{ }^\circ\text{C}$ ; typical values  
 (2)  $T_j = 150 \text{ }^\circ\text{C}$ ; maximum values  
 (3)  $T_j = 25 \text{ }^\circ\text{C}$ ; maximum values

**Fig. 11. On-state current as a function of on-state voltage**



**Fig. 12. Normalized gate trigger voltage as a function of junction temperature**

10. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247

SOT429N

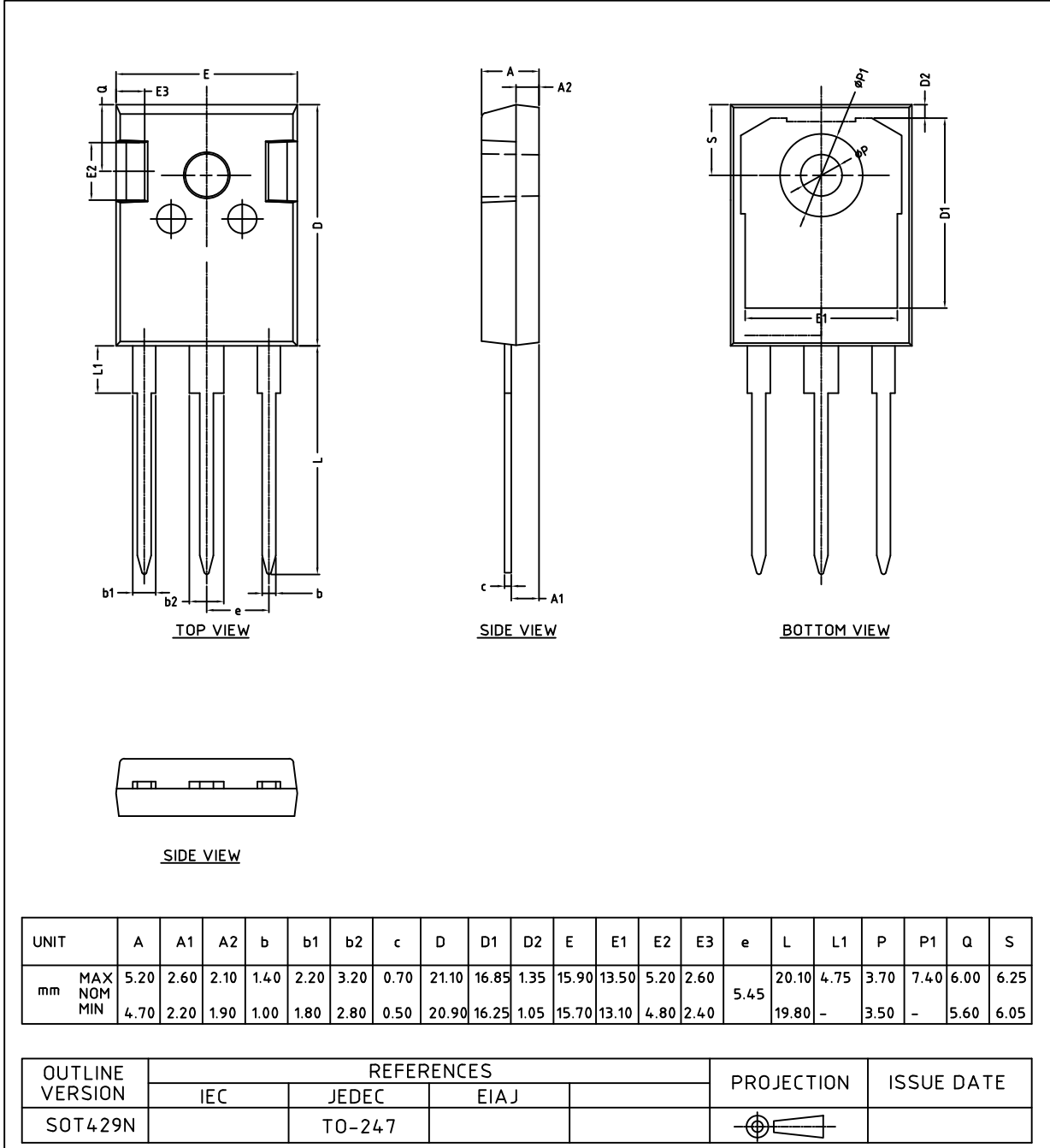


Fig. 13. Package outline TO-247 (SOT429N)

## 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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**Телефон:** 8 (812) 309 58 32 (многоканальный)

**Факс:** 8 (812) 320-02-42

**Электронная почта:** [org@eplast1.ru](mailto:org@eplast1.ru)

**Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.